

## **N-Channel MOSFET**

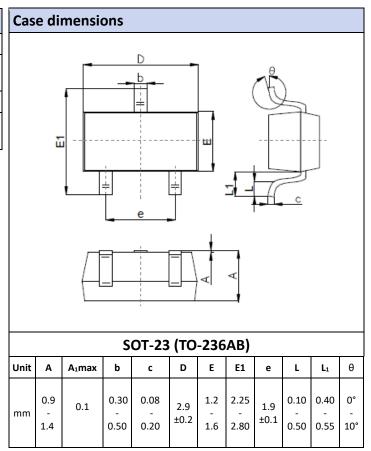
Primary characteristics				
Symbol	Parameter	Value	Unit	
I <sub>D</sub>	Continuous drain current (@Ta=25°C)	340	mA	
V <sub>DS</sub>	Drain source voltage	50	V	
R <sub>DSON</sub> @V <sub>GS</sub> =4.5V	Static drain-source on- resistance	3.0	Ω	

## **Features**

- **SOT-23** case for easy automatic insertion
- Pb-free and RoHS compliant
- Low input Capacitance
- Fast Switching Speed
- Low Input / Output Leakage
- Voltage controlled small signal switch

# **Application**

- Battery operated systems
- Solid-state relays
- Direct logic-level interface: TTL/CMOS



Absolute maximum ratings (T <sub>A</sub> = 25°C unless otherwise noted)					
Characteristic	Symbol	Value	Unit		
Drain-source voltage	V <sub>DS</sub>	50	V		
Gate-source voltage	V <sub>GS</sub>	±20	V		
Continuous drain current	ID	340	mA		
Pulsed drain current <sup>1</sup>	I <sub>DM</sub>	1.5	Α		
Power Dissipation <sup>2</sup>	P <sub>D</sub>	350	mW		
Operating junction temperature range	T <sub>J</sub> , T <sub>STG</sub>	-55 ~ 150	°C		
Thermal resistance junction-ambient <sup>2</sup>	R <sub>eJA</sub>	357	°C/W		

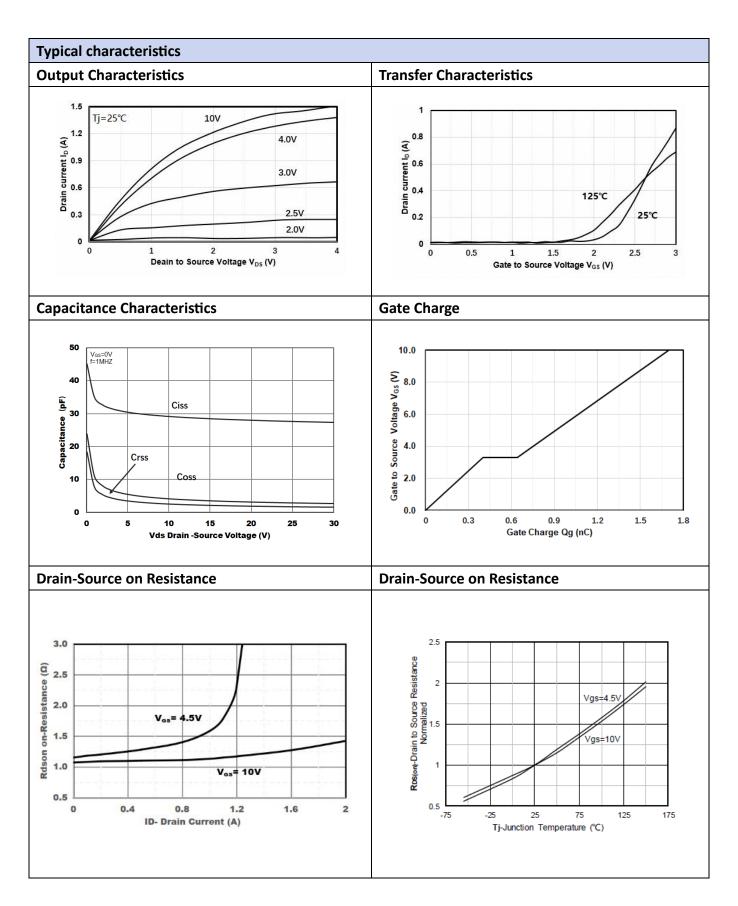


Characteristic	Test condition	Symphol		Value		Unit
Characteristic	lest condition	Symbol	Min.	Тур.	Max.	
Drain-source breakdown voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	V <sub>DSS</sub>	50	-	-	V
Zero gate voltage drain current	$V_{DS}$ =50V, $V_{GS}$ =0V	I <sub>DSS</sub>	-	-	1.0	μΑ
Gate-body leakage current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	lgss	-	-	±100	nA
Gate threshold voltage	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	V <sub>GS(th)</sub>	0.8	1.2	1.6	V
Static drain-source on-state resistance <sup>3</sup>	$V_{GS}$ =10V, $I_D$ =300mA	D	-	1.1	2.5	Ω
Static drain-source on-state resistance	V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	R <sub>DS(ON)</sub>	-	2.2	3.0	
On state drain current	V <sub>GS</sub> =10V, V <sub>DS</sub> =5.0V	I <sub>D(ON)</sub>	680	-	-	mA
Dynamic electrical characteristics						
Chamatanistia		Comple	Value			
Characteristic	Test condition	Symbol	Min.	Тур.	Max.	Unit
Input capacitance	V <sub>DS</sub> =25V	Ciss	-	28.5	-	
Output capacitance	V <sub>GS</sub> =0V	Coss	-	2.7	-	pF
Reverse transfer capacitance	f=1.0MHz	Crss	-	1.78	-	
Total gate charge	V <sub>DS</sub> =25V	Qg	-	1.7	2.5	nC
Gate source charge	V <sub>GS</sub> =10V	Qgs	-	0.4	-	
Gate drain charge	I <sub>D</sub> =300mA	Q <sub>gd</sub>	-	0.24	-	
Switching characteristics						
Characteristic	Test condition	Cumahal		Value		l lmin
Characteristic	rest condition	Symbol	Min.	Тур.	Max.	Unit
Turn on delay time	V <sub>DS</sub> =25V	t <sub>d(ON)</sub>	-	2.6	-	
Turn on rise time	V <sub>GS</sub> =10V	t <sub>r</sub>	-	18.8	-	nc
Turn off delay time	I <sub>D</sub> =300mA	t <sub>d(OFF)</sub>	-	9.7	-	ns
Turn off fall time	$R_G=6.0\Omega$	t <sub>f</sub>	-	47	-	
Source drain diode characteristics						
Characteristic	Test condition	Symbol		Value		l lmia
Characteristic			Min.	Тур.	Max.	Unit
Maximum body-diode continuous current	<b>T</b> <sub>A</sub> =25°C	I <sub>SD</sub>	-	-	340	mA
Diode forward voltage	I <sub>S</sub> =300mA, V <sub>GS</sub> =0V	V <sub>SD</sub>	_	_	1.2	V

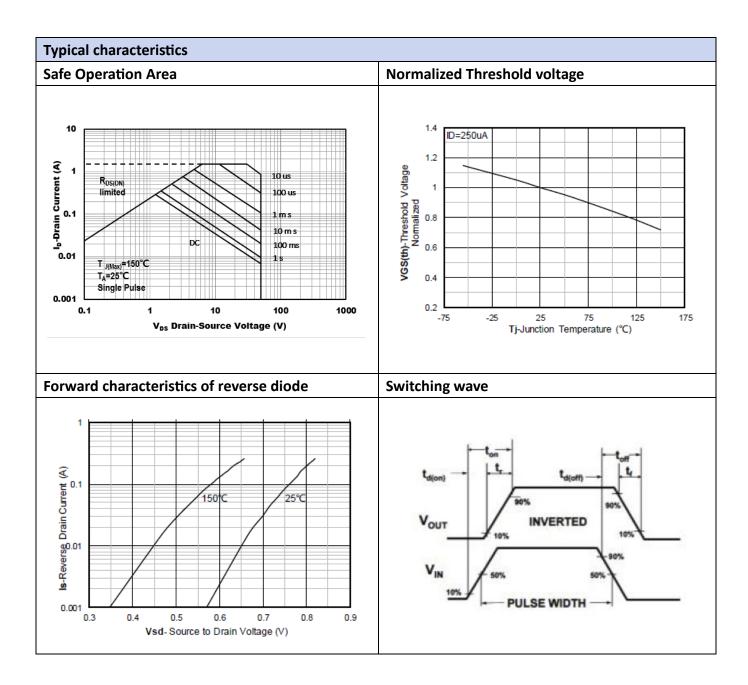
#### Notes:

- 1. Pulse width limited by maximum allowable junction temperature.
- 2. The value of PD&R $\theta$ JA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, double sided, in a still air environment with Ta=25 $^{\circ}$ C.
- 3. Pulse test; Pulse width≤300us, duty cycle ≤ 2%

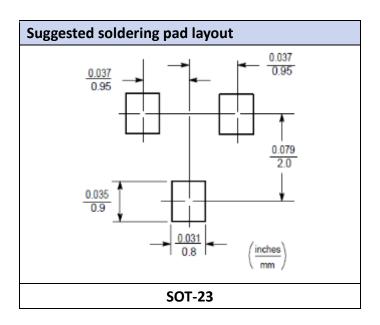












Ordering information			
Part Number	Package	Shipping Quantity	Dimensions
BSS138	SOT-23	3000 pcs / 7" reel	

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